Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT89 plastic package.

PNP complement: PBSS5350X

2. Features and benefits

- SOT89 (SC-62) package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- · Higher efficiency leading to less heat generation
- Reduced printed-circuit board requirements
- AEC-Q101 qualified

3. Applications

- Power management
 - · DC/DC converters
 - · Supply line switching
 - Battery charger
 - LCD backlighting
- Peripheral drivers
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|---|--|-----|-----|-----|------|
| V _{CBO} | collector-base voltage | open emitter | - | - | 50 | V |
| I _C | collector current | | - | - | 3 | Α |
| I _{CM} | peak collector current | limited by T _{j(max)} | - | - | 5 | Α |
| R _{CEsat} | collector-emitter saturation resistance | I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 100 | 130 | mΩ |



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|----------------|
| 1 | Е | emitter | | С |
| 2 | С | collector | | |
| 3 | В | base | | B—(|
| | | | 3 2 1 | E |
| | | | SOT89 | sym123 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|---------|--|---------|--|--|
| | Name | Description | Version | | |
| PBSS4350X | | plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body | SOT89 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBSS4350X | S43 |

8. Limiting values

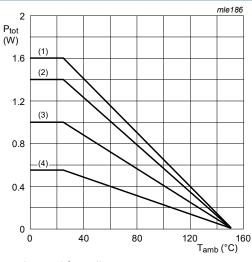
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------|--------------------------------|-----|-----|-----|------|
| V_{CBO} | collector-base voltage | open emitter | | - | 50 | V |
| V_{CEO} | collector-emitter voltage | open base | | - | 50 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | 5 | V |
| Ic | collector current | | | - | 3 | А |
| I _{CM} | peak collector current | limited by T _{j(max)} | | - | 5 | А |
| I _B | base current | | | - | 0.5 | Α |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C | [1] | - | 550 | mW |
| | | | [2] | - | 1 | W |
| | | | [3] | - | 1.4 | W |
| | | | [4] | - | 1.6 | W |
| Tj | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -65 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB 7 cm², single-sided copper, tin-plated.

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- (1) Ceramic PCB; 7 cm² mounting pad for collector (2) FR4 PCB; 6 cm² copper mounting pad for collector (3) FR4 PCB; 1 cm² copper mounting pad for collector

- (4) Standard footprint

Fig. 1. **Power derating curves**

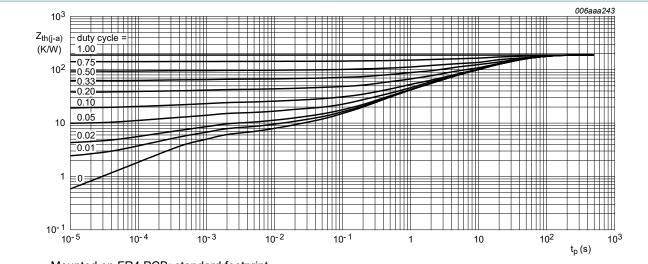
9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|---------------------|-----|-----|-----|-----|------|
| ui(j-a) | thermal resistance from | junction to ambient | [1] | - | - | 225 | K/W |
| | junction to ambient | | [2] | - | - | 125 | K/W |
| | | [3] | [3] | - | - | 90 | K/W |
| | | | [4] | - | - | 80 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | - | 16 | K/W |

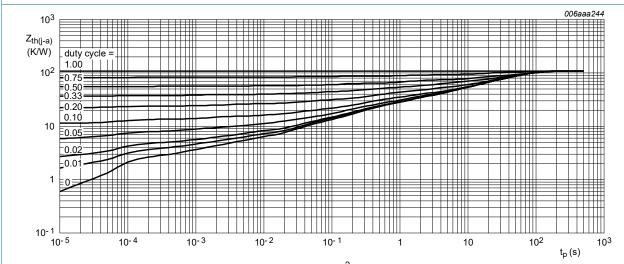
- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². [3]
- Device mounted on a ceramic PCB 7 cm², single-sided copper, tin-plated.

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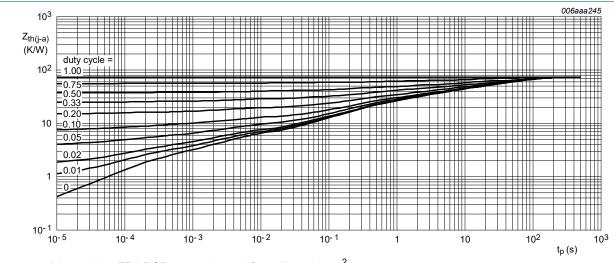
Mounted on FR4 PCB; standard footprint.

Fig. 2. Transient thermal impedance as a function of pulse duration; typical values



Mounted on FR4 PCB; mounting pad for collector 1 cm²

Fig. 3. Transient thermal impedance as a function of pulse duration; typical values



Mounted on FR4 PCB; mounting pad for collector 6 cm²

Fig. 4. Transient thermal impedance as a function of pulse duration; typical values

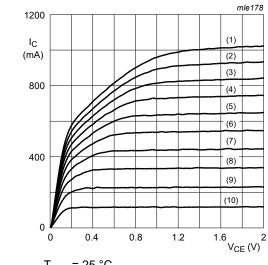
50 V, 3 A NPN low VCEsat transistor

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|----------------------|---|--|-----|-----|-----|------|
| V _{(BR)CBO} | collector-base breakdown voltage | $I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$ | 50 | - | - | V |
| V _{(BR)CEO} | collector-emitter breakdown voltage | $I_C = 10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$ | 50 | - | - | V |
| V _{(BR)EBO} | emitter-base breakdown voltage (collector open) | $I_E = 100 \mu A; I_C = 0 A; T_{amb} = 25 °C$ | 5 | - | - | V |
| СВО | collector-base cut-off | V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| | current | $V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$ | - | - | 50 | μΑ |
| I _{CES} | collector-emitter cut-off current | V _{CE} = 50 V; V _{BE} = 0 V; T _{amb} = 25 °C | - | - | 100 | nA |
| ЕВО | emitter-base cut-off current | V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C | - | - | 100 | nA |
| h _{FE} | DC current gain | V_{CE} = 2 V; I_{C} = 0.1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 2; T_{amb} = 25 °C | 300 | - | - | |
| | | V_{CE} = 2 V; I_{C} = 0.5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | 300 | - | - | |
| | | V_{CE} = 2 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C | 300 | - | 700 | |
| | | V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C | 200 | - | - | |
| | | V_{CE} = 2 V; I_{C} = 3 A; pulsed; $t_{p} \le 300 \mu s$; δ ≤ 0.02; T_{amb} = 25 °C | 100 | - | - | |
| V _{CEsat} | collector-emitter | I _C = 0.5 A; I _B = 50 mA; T _{amb} = 25 °C | - | - | 80 | mV |
| | saturation voltage | I _C = 1 A; I _B = 50 mA; T _{amb} = 25 °C | - | - | 160 | mV |
| | | I_C = 2 A; I_B = 100 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | - | 280 | mV |
| | | I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | - | 260 | mV |
| | | I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | - | 370 | mV |
| R _{CEsat} | collector-emitter saturation resistance | I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | 100 | 130 | mΩ |
| V _{BEsat} | base-emitter saturation | I _C = 2 A; I _B = 100 mA; T _{amb} = 25 °C | - | - | 1.1 | V |
| | voltage | I_C = 3 A; I_B = 300 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C | - | - | 1.2 | V |
| V_{BEon} | base-emitter turn-on voltage | V _{CE} = 2 V; I _C = 1 A; T _{amb} = 25 °C | - | - | 1.1 | V |
| ŤТ | transition frequency | V _{CE} = 5 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C | 100 | - | - | MHz |
| O _c | collector capacitance | V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C | - | - | 25 | pF |

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 T_{amb} = 25 °C

(1) $I_B = 2600 \mu A$

(2) $I_B = 2340 \mu A$

 $(3) I_B = 2080 \mu A$

 $(4) I_B = 1820 \mu A$

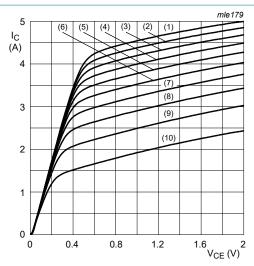
 $(5) I_B = 1560 \mu A$ (6) $I_B = 1300 \mu A$

(7) $I_B = 1040 \mu A$ (8) $I_B = 780 \, \mu A$

(9) $I_B = 520 \mu A$

 $(10) I_B = 260 \mu A$

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



 T_{amb} = 25 °C

(1) $I_B = 120 \text{ mA}$

(2) I_B = 108 mA (3) I_B = 96 mA

 $(4) I_B = 84 \text{ mA}$

 $(5) I_{B} = 72 \text{ mA}$

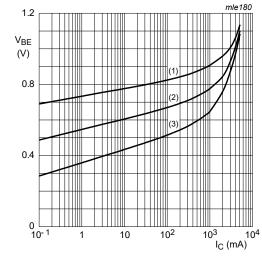
(6) $I_B = 60 \text{ mA}$ $(7) I_B = 48 \text{ mA}$

(8) $I_B = 36 \text{ mA}$

(9) $I_B = 24 \text{ mA}$

 $(10) I_B = 12 mA$

Fig. 6. Collector current as a function of collectoremitter voltage; typical values

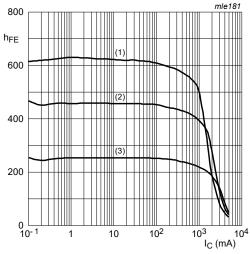


 $V_{CE} = 2 V$

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 7. Base-emitter voltage as a function of collector current; typical values

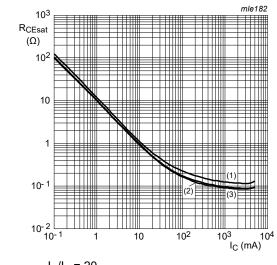


 $V_{CE} = 2 V$ (1) $T_{amb} = 100 °C$

(2) T_{amb} = 25 °C (3) T_{amb} = -55 °C

Fig. 8. DC current gain as a function of collector current; typical values

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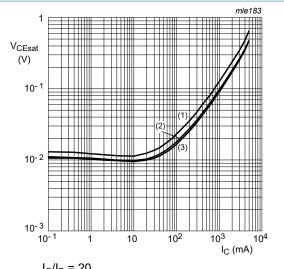


$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Fig. 9. Equivalent on-resistance as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \,^{\circ}C$$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

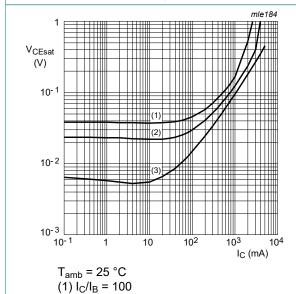
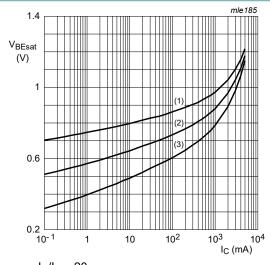


Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B}=20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 12. Base-emitter saturation voltage as a function of collector current; typical values

11. Test information

(2) $I_C/I_B = 50$

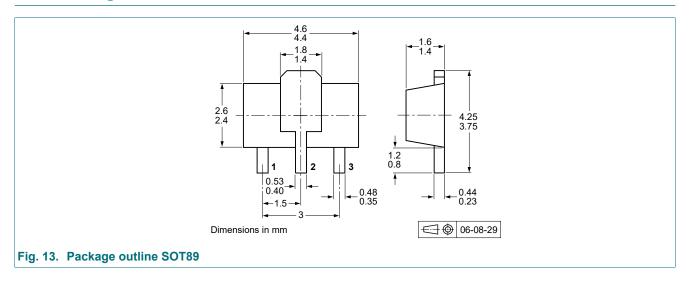
(3) $I_C/I_B = 10$

Quality information

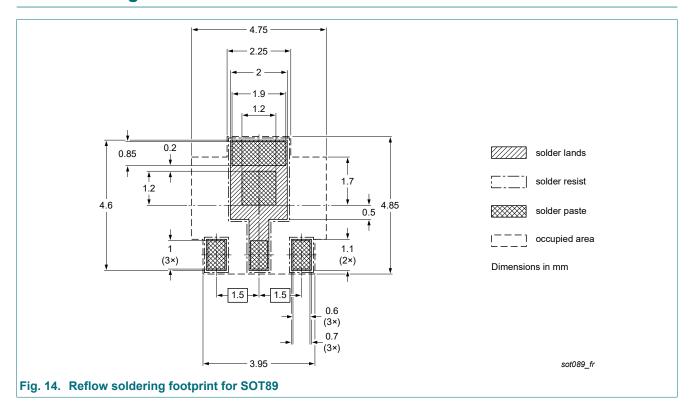
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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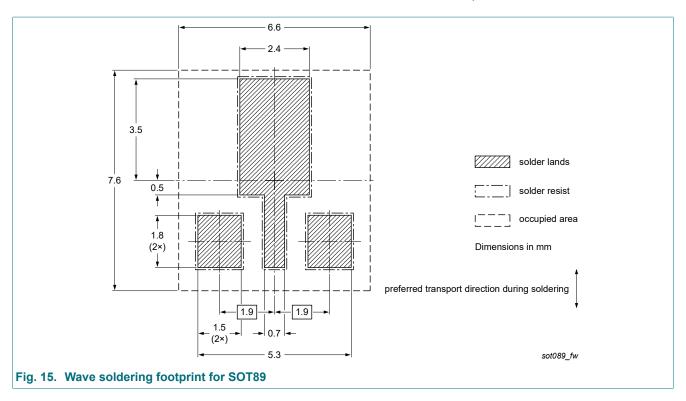
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

| 10010 01 110 1101011 1110 | , | | | | | |
|---------------------------|---|--------------------|---------------|---------------|--|--|
| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes | | |
| PBSS4350X v.3 | 20220516 | Product data sheet | - | PBSS4350X v.2 | | |
| Modifications: | The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. | | | | | |
| PBSS4350X v.2 | 20041104 | Product data sheet | - | PBSS4350X v.1 | | |
| PBSS4350X v.1 | 20031121 | Product data sheet | - | - | | |

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15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- Please consult the most recently issued document before initiating or completing a design.
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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 16 May 2022

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